

General Description

The MDI6N60B uses advanced MagnaChip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

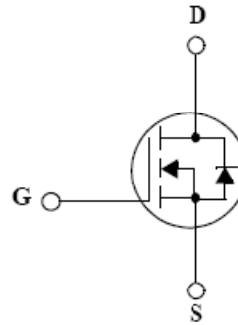
MDI6N60B is suitable device for SMPS, high Speed switching and general purpose applications.

Features

- $V_{DS} = 600V$
- $I_D = 4.5A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} \leq 1.45\Omega$ @ $V_{GS} = 10V$

Applications

- Power Supply
- PFC
- Ballast



Absolute Maximum Ratings (Ta = 25°C)

| Characteristics | Symbol | Rating | Unit | |
|--|----------------|--------------------|------|------|
| Drain-Source Voltage | V_{DSS} | 600 | V | |
| Gate-Source Voltage | V_{GSS} | ±30 | V | |
| Continuous Drain Current | I_D | $T_C=25^\circ C$ | 4.5* | A |
| | | $T_C=100^\circ C$ | 2.8* | A |
| Pulsed Drain Current ⁽¹⁾ | I_{DM} | 18* | A | |
| Power Dissipation | P_D | $T_C=25^\circ C$ | 73 | W |
| | | Derate above 25 °C | 0.59 | W/°C |
| Repetitive Avalanche Energy ⁽¹⁾ | E_{AR} | 7.3 | mJ | |
| Peak Diode Recovery dv/dt ⁽³⁾ | dv/dt | 4.5 | V/ns | |
| Single Pulse Avalanche Energy ⁽⁴⁾ | E_{AS} | 140 | mJ | |
| Junction and Storage Temperature Range | T_J, T_{stg} | -55~150 | °C | |

※ I_D limited by maximum junction temperature

Thermal Characteristics

| Characteristics | Symbol | Rating | Unit |
|--|-----------------|--------|------|
| Thermal Resistance, Junction-to-Ambient ⁽¹⁾ | $R_{\theta JA}$ | 110 | °C/W |
| Thermal Resistance, Junction-to-Case ⁽¹⁾ | $R_{\theta JC}$ | 1.7 | |

Ordering Information

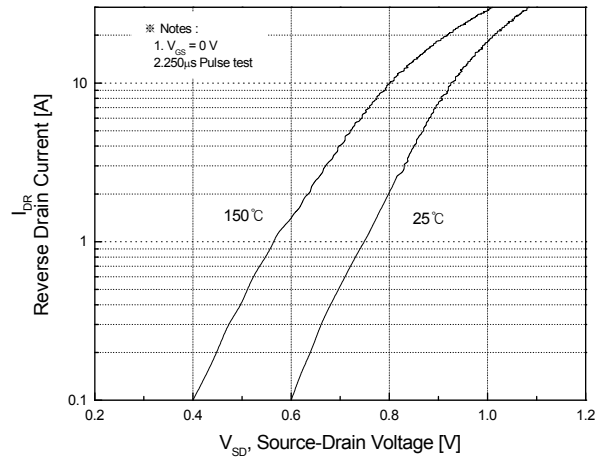
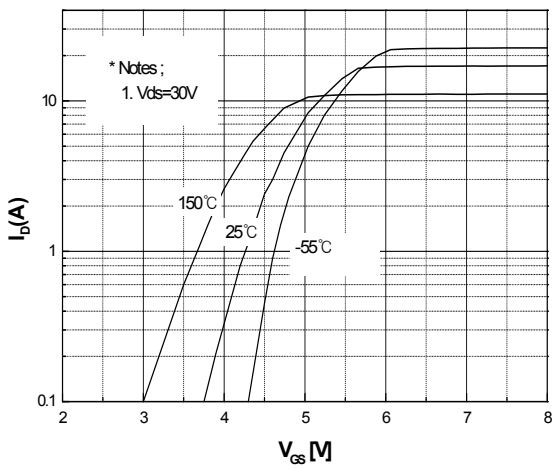
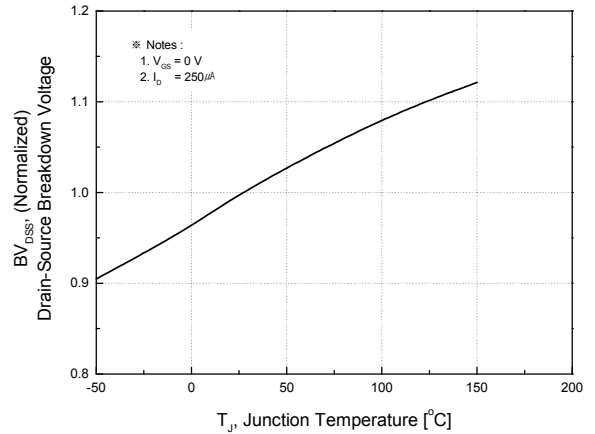
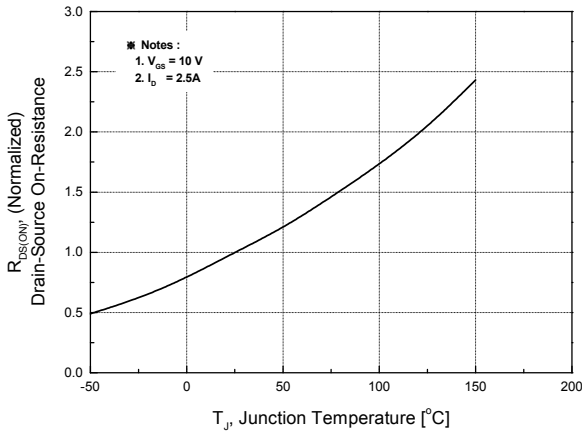
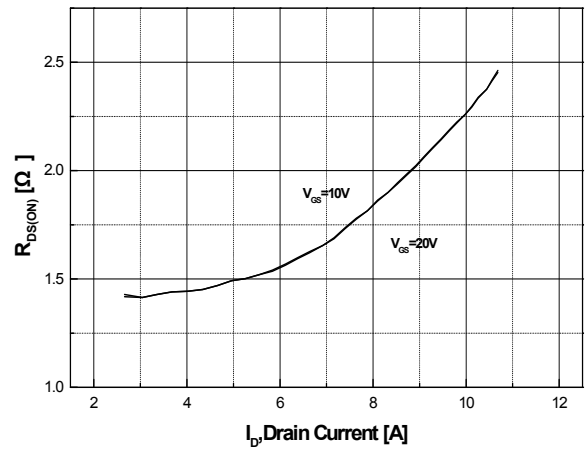
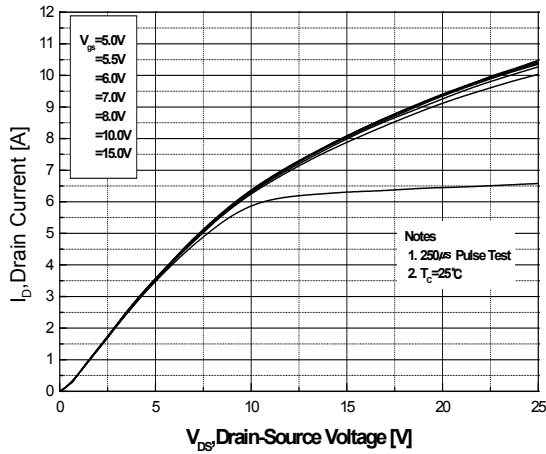
| Part Number | Temp. Range | Package | Packing | RoHS Status |
|-------------|-------------|---------|---------|--------------|
| MDI6N60BTH | -55~150°C | I-PAK | Tube | Halogen Free |

Electrical Characteristics (Ta =25°C)

| Characteristics | Symbol | Test Condition | Min | Typ | Max | Unit |
|--|--------------|---|-----|------|------|----------|
| Static Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $I_D = 250\mu A, V_{GS} = 0V$ | 600 | - | - | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = 250\mu A$ | 2.0 | - | 4.0 | |
| Drain Cut-Off Current | I_{DSS} | $V_{DS} = 600V, V_{GS} = 0V$ | - | - | 1 | μA |
| Gate Leakage Current | I_{GSS} | $V_{GS} = \pm 30V, V_{DS} = 0V$ | - | - | 100 | nA |
| Drain-Source ON Resistance | $R_{DS(ON)}$ | $V_{GS} = 10V, I_D = 2.25A$ | - | 1.2 | 1.45 | Ω |
| Forward Transconductance | g_{fs} | $V_{DS} = 30V, I_D = 2.25A$ | - | 5 | - | S |
| Dynamic Characteristics | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = 480V, I_D = 6.0A, V_{GS} = 10V^{(3)}$ | - | 13.6 | - | nC |
| Gate-Source Charge | Q_{gs} | | - | 2.5 | - | |
| Gate-Drain Charge | Q_{gd} | | - | 4.5 | - | |
| Input Capacitance | C_{iss} | $V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$ | - | 684 | - | pF |
| Reverse Transfer Capacitance | C_{rss} | | - | 3.4 | - | |
| Output Capacitance | C_{oss} | | - | 77 | - | |
| Turn-On Delay Time | $t_{d(on)}$ | $V_{GS} = 10V, V_{DS} = 250V, I_D = 6.0A, R_G = 25\Omega^{(3)}$ | - | 14.3 | - | ns |
| Rise Time | t_r | | - | 18.2 | - | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 50.6 | - | |
| Fall Time | t_f | | - | 24.5 | - | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Maximum Continuous Drain to Source Diode Forward Current | I_S | | - | 6 | - | A |
| Source-Drain Diode Forward Voltage | V_{SD} | $I_S = 6.0A, V_{GS} = 0V$ | - | | 1.4 | V |
| Body Diode Reverse Recovery Time | t_{rr} | $I_F = 6.0A, di/dt = 100A/\mu s^{(3)}$ | - | 275 | - | ns |
| Body Diode Reverse Recovery Charge | Q_{rr} | | - | 2.1 | - | μC |

Note :

- Pulse width is based on $R_{\theta JC}$ & $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C.
- Pulse test: pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ C$.
- $I_{SD} \leq 6.0A, di/dt \leq 200A/\mu s, V_{DD} \leq BV_{DSS}, R_g = 25\Omega$, Starting $T_J = 25^\circ C$
- $L = 7.2mH, I_{AS} = 6.0A, V_{DD} = 50V, R_g = 25\Omega$, Starting $T_J = 25^\circ C$



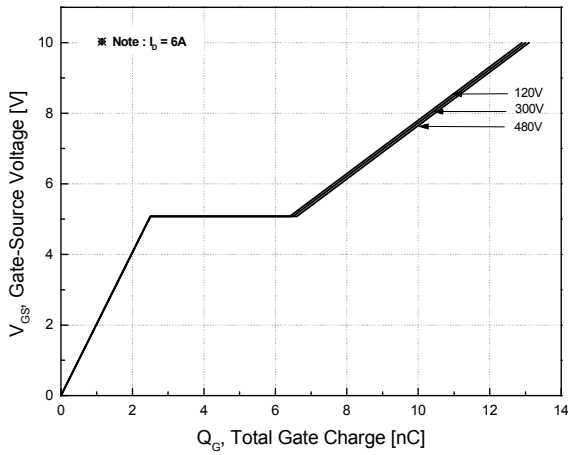


Fig.7 Gate Charge Characteristics

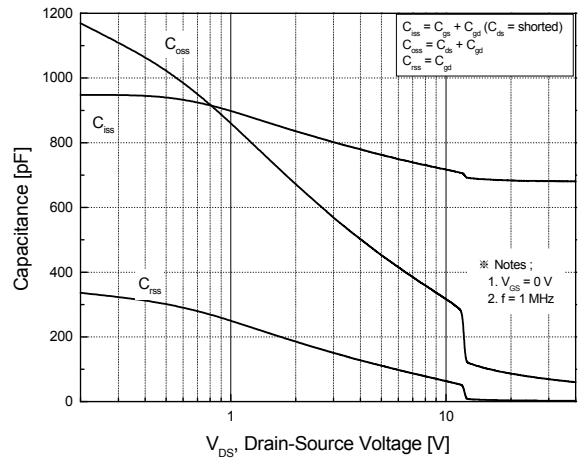


Fig.8 Capacitance Characteristics

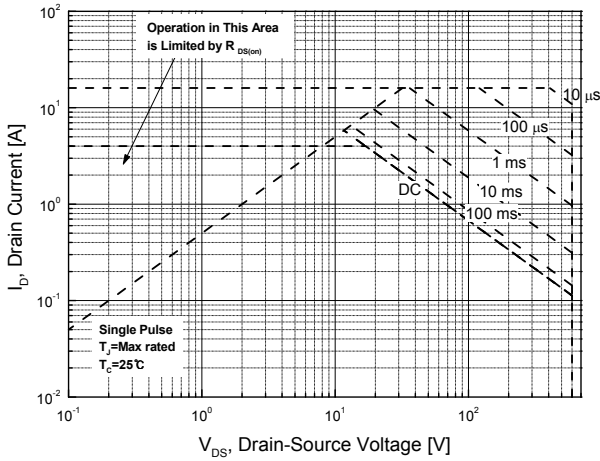


Fig.9 Maximum Safe Operating Area

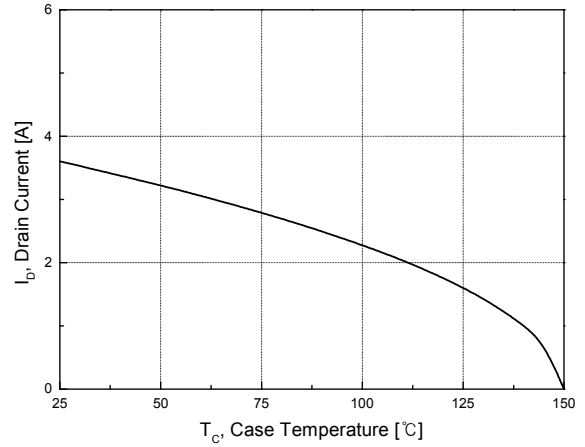


Fig.10 Maximum Drain Current vs. Case Temperature

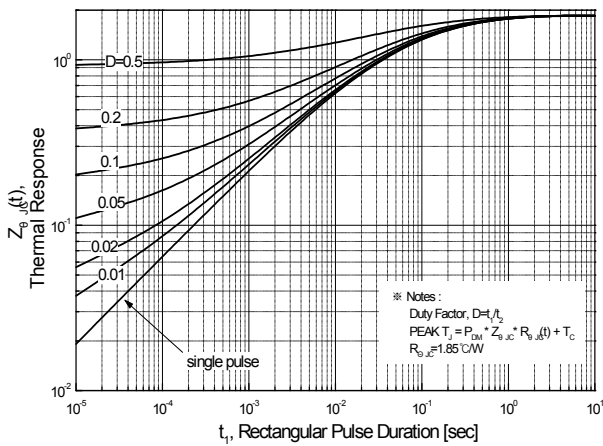


Fig.11 Transient Thermal Response Curve

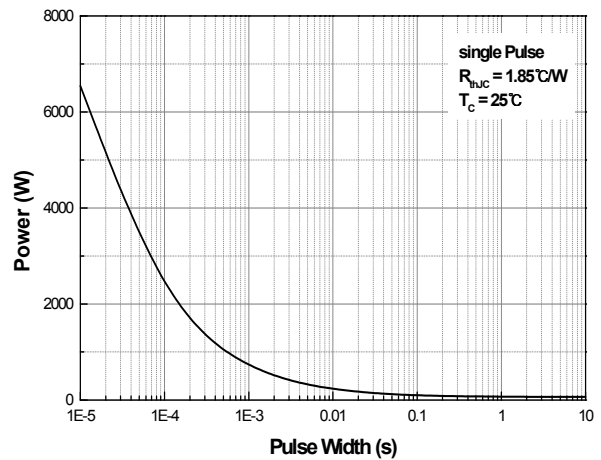
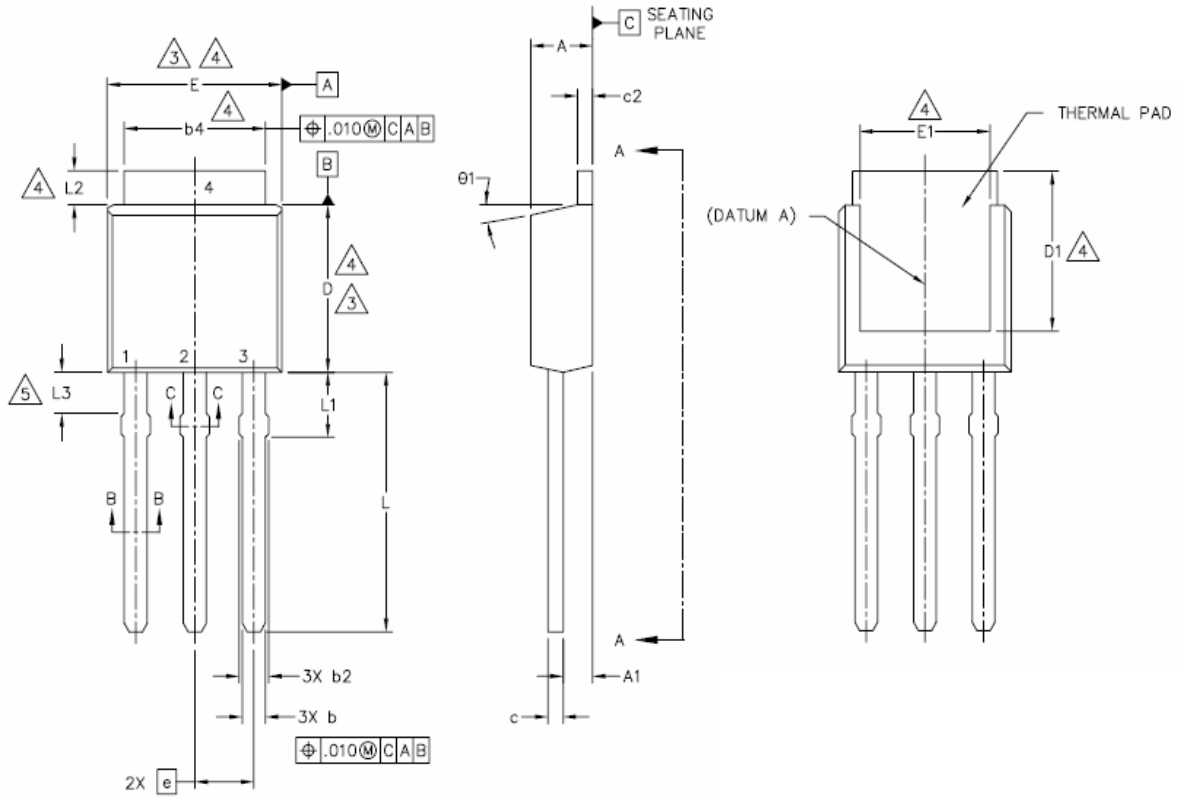


Fig.12 Single Pulse Maximum Power Dissipation

Physical Dimension

TO-251 (IPAK)

Dimensions are in millimeters unless otherwise specified



| SYMBOL | MIN | NOM | MAX |
|--------|----------|------|------|
| A | 2.18 | - | 2.39 |
| A1 | 0.89 | - | 1.14 |
| b | 0.64 | - | 0.89 |
| b1 | 0.64 | 0.71 | 0.79 |
| b2 | 0.76 | - | 1.14 |
| b4 | 4.95 | - | 5.46 |
| c | 0.46 | - | 0.61 |
| c2 | 0.46 | - | 0.89 |
| D | 5.97 | 6.10 | 6.22 |
| D1 | 4.75 | - | |
| E | 6.35 | - | 6.73 |
| E1 | 4.32 | - | 0.00 |
| e | 2.30 BSC | | |
| L | 8.89 | - | 9.65 |
| L1 | 1.80 | - | 2.29 |
| L2 | 0.70 | - | 1.27 |
| L3 | 1.14 | - | 1.52 |

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